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## **ON Semiconductor**®

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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="mailto:www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="mailto:Fairchild\_questions@onsemi.com">Fairchild\_questions@onsemi.com</a>.

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### PCFFS05120AF Silicon Carbide Schottky Diode 1200 V, 5 A

#### Features

- Max Junction Temperature 175 °C
- Avalanche Rated 55 mJ
- · High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

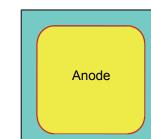
#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

#### **Die Information**

# Wafer Diameter 6 inch Die Size 1,690 x 1,690 μm (include Scribe Lane) Metallization

- $\begin{array}{ccc} \cdot \mbox{ Top } & Ti \ / \ TiN \ / \ Al \ 4\mu m \\ \cdot \ Back & Ti \ / \ NiV \ / \ Ag \\ \bullet \ Die \ Thickness & Typ. \ 200\mu m \\ \bullet \ Bonding \ Pad \ Size \\ \cdot \ Anode & 1,110 \times 1,110 \ \mu m \end{array}$
- Recommended Wire Bond (Note 1)
   · Anode 12mil × 1



#### Electrical Characteristics on Wafer (Note 2) T<sub>C</sub> = 25°C unless otherwise noted

| Symbol         | Parameter                | Test Conditions                                 | Min. | Тур. | Max. | Unit |
|----------------|--------------------------|---|------|------|------|------|
| V <sub>R</sub> | Reverse Blocking Voltage | I <sub>R</sub> = 200 μA, T <sub>C</sub> = 25 °C | 1200 | -    | -    | V    |
| V <sub>F</sub> | Forward Voltage          | I <sub>F</sub> = 5A, T <sub>C</sub> = 25 °C     | 1.20 | -    | 1.75 | V    |
| I <sub>R</sub> | Reverse Current          | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25 °C | -    | -    | 200  | μΑ   |

Notes:

1. Based on TO-247 package of ON Semiconductor

2. Tested 100% on wafer

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Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and

higher reliability compared to Silicon. No reverse recovery cur-

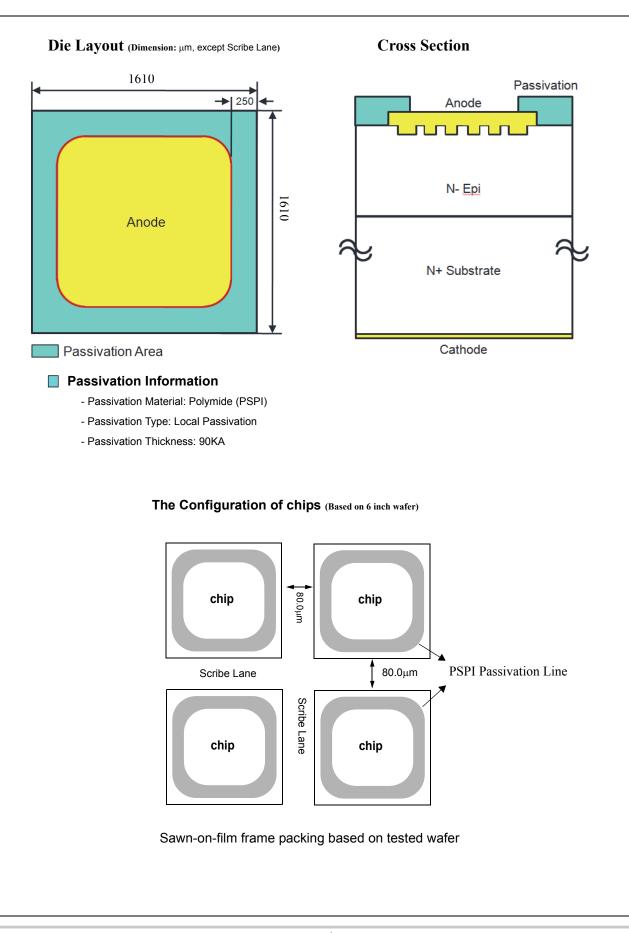
rent, temperature dependent switching characteristics, and

excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include

highest efficiency, faster operation frequency, increased power

density, reduced EMI, and reduced system size and cost.

Description



| Absolute Maximum Ratings on TO-247 Package T <sub>C</sub> = 25 °C unless otherwise noted |
|--|
|--|

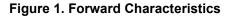
| Symbol                            | Parameter  | Ratings                                 | Unit        |    |
|-----------------------------------|--|---|-------------|----|
| V <sub>RRM</sub>                  | Peak Repetitive Reverse Voltage                    |   | 1200        | V  |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy (Note 3)             |   | 55          | mJ |
| I <sub>F</sub>                    | Continuous Rectified Forward Current @ Tc < 148 °C |   | 5           | Α  |
| I <sub>F, Max</sub>               | Non-Repetitive Peak Forward Surge Current          | T <sub>C</sub> = 25 °C, 10 μs           | 380         | Α  |
|                                   |  | T <sub>C</sub> = 150 °C, 10 μs          | 330         | Α  |
| I <sub>F,SM</sub>                 | Non-Repetitive Forward Surge Current               | Half-Sine Pulse, $t_p = 8.3 \text{ ms}$ | 42          | Α  |
| I <sub>F,RM</sub>                 | Repetitive Forward Surge Current                   | Half-Sine Pulse, $t_p = 8.3 \text{ ms}$ | 21          | Α  |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range            |   | -55 to +175 | °C |

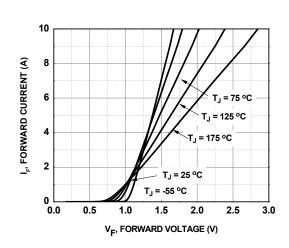
### Electrical Characteristics on TO-247 Package T<sub>C</sub> = 25 °C unless otherwise noted.

| Symbol         | Parameter               | Test Conditions  | Min. | Тур. | Max. | Unit |
|----------------|-------------------------|--|------|------|------|------|
| V <sub>F</sub> | Forward Voltage         | I <sub>F</sub> = 5 A, T <sub>C</sub> = 25 <sup>o</sup> C     | -    | 1.45 | 1.75 | V    |
|                |                         | I <sub>F</sub> = 5 A, T <sub>C</sub> = 125 °C                | -    | 1.7  | 2    |      |
|                |                         | I <sub>F</sub> = 5 A, T <sub>C</sub> = 175 <sup>o</sup> C    | -    | 2    | 2.4  |      |
| I <sub>R</sub> | Reverse Current         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 25 °C              | -    | -    | 200  | μА   |
|                |                         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 125 °C             | -    | -    | 300  |      |
|                |                         | V <sub>R</sub> = 1200 V, T <sub>C</sub> = 175 <sup>o</sup> C | -    | -    | 400  |      |
| Q <sub>C</sub> | Total Capacitive Charge | V = 800 V  | -    | 37   | -    | nC   |
| С              | Total Capacitance       | V <sub>R</sub> = 1 V, f = 100 kHz                            | -    | 337  | -    | pF   |
|                |                         | V <sub>R</sub> = 400 V, f = 100 kHz                          | -    | 33   | -    |      |
|                |                         | V <sub>R</sub> = 800 V, f = 100 kHz                          | -    | 26   | -    |      |

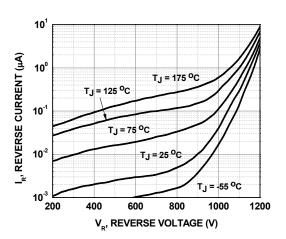
Note 3: EAS of 55 mJ is based on starting T\_J = 25 °C, L = 0.5 mH, I\_{AS} = 15A, V = 150 V.

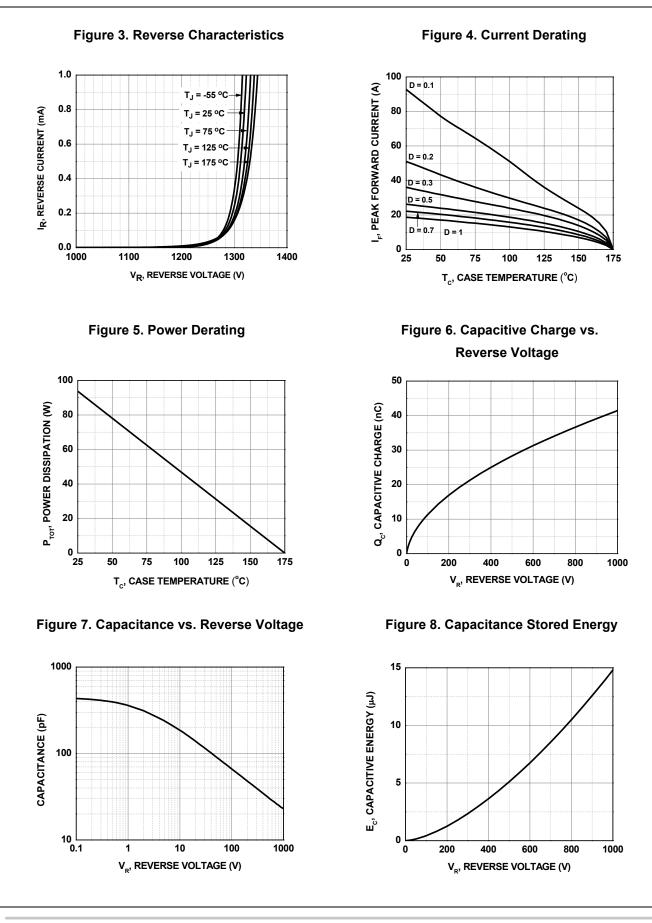
#### Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted.





#### Figure 2. Reverse Characteristics





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